



Description

JMT N-channel MOSFET

Features

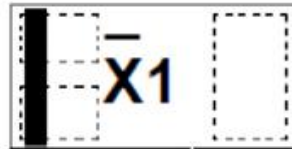
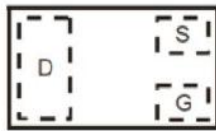
- $V_{DS}=60V$, $I_D=0.2A$
 $R_{DS(ON)} < 2.2\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 2.8\Omega @ V_{GS} = 5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired
- ESD Protected: 2KV

Application

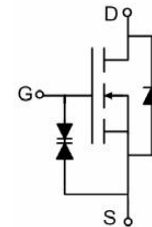
- Battery Operated Systems
- Direct logic-level Interface: TTL/CMOS
- Solid-State Relays



DFN1006-3L



Marking and pin Assignment



Schematic diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
X1	JMTD2N7002KS	TAPING	DFN1006-3L	7inch	10000	400000

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ C$	0.2
		$T_A = 100^\circ C$	0.13
I_{DM}	Pulsed Drain Current ^{note1}	0.8	A
P_D	Power Dissipation	$T_A = 25^\circ C$	0.15
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	833	$^\circ C/W$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ C$



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = 250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} = 0V,	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±10	uA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note2</small>	V _{GS} =10V, I _D =0.3A	-	1.66	2.2	Ω
		V _{GS} =4.5V, I _D =0.2A	-	2.0	2.8	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	28	-	pF
C _{oss}	Output Capacitance		-	11	-	pF
C _{rss}	Reverse Transfer Capacitance		-	4	-	pF
Q _g	Total Gate Charge	V _{DS} = 10V, I _D = 0.3A, V _{GS} = 4.5V	-	1.7	-	nC
Q _{gs}	Gate-Source Charge		-	0.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	0.6	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = 30V, I _D =0.2A, R _{GEN} = 10Ω, V _{GS} =10V,	-	10	-	ns
t _r	Turn-on Rise Time		-	50	-	ns
t _{d(off)}	Turn-off Delay Time		-	17	-	ns
t _f	Turn-off Fall Time		-	10	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	0.2	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	0.8	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =0.2A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%



Typical Performance Characteristics

Figure 1: Output Characteristics

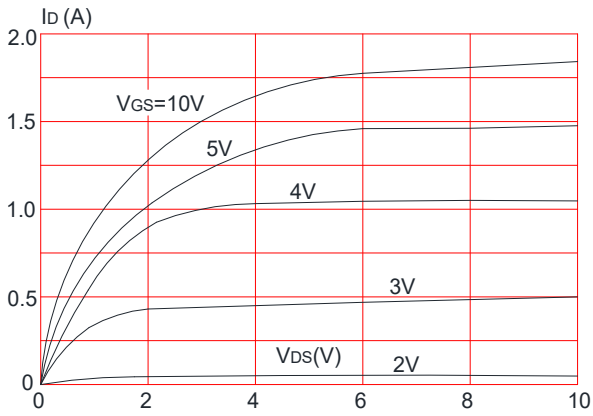


Figure 2: Typical Transfer Characteristics

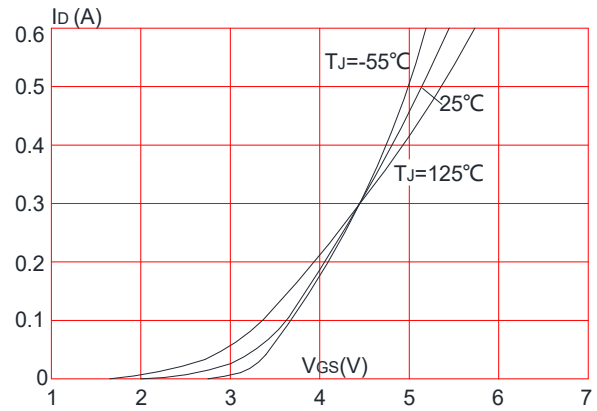


Figure 3: On-resistance vs. Drain Current

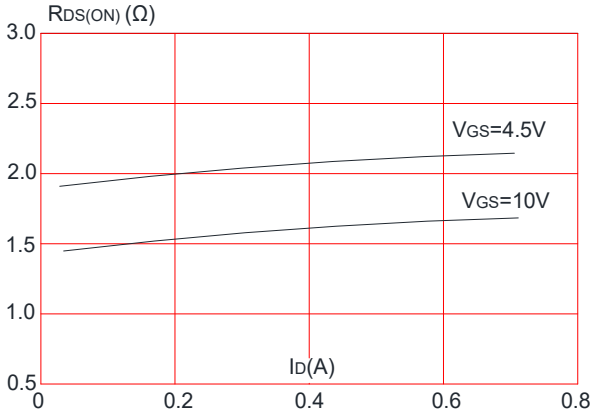


Figure 4: Body Diode Characteristics

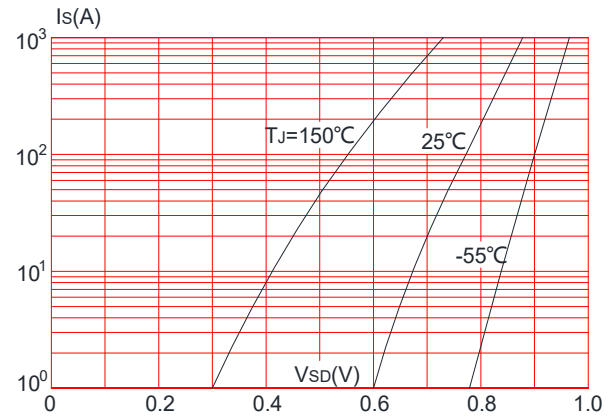


Figure 5: Gate Charge Characteristics

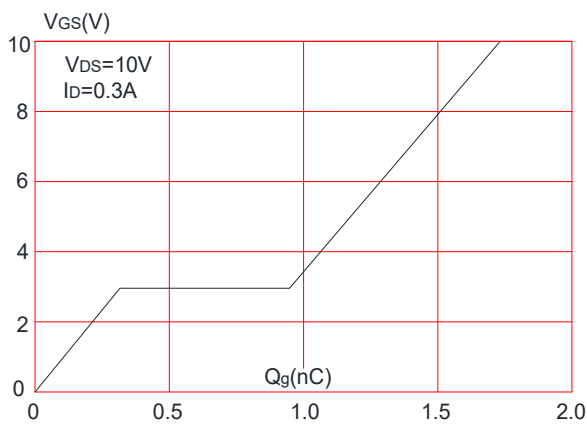
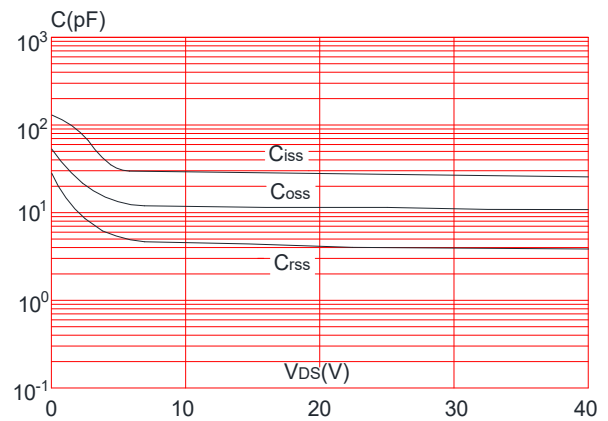


Figure 6: Capacitance Characteristics





JMTD2N7002KS

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

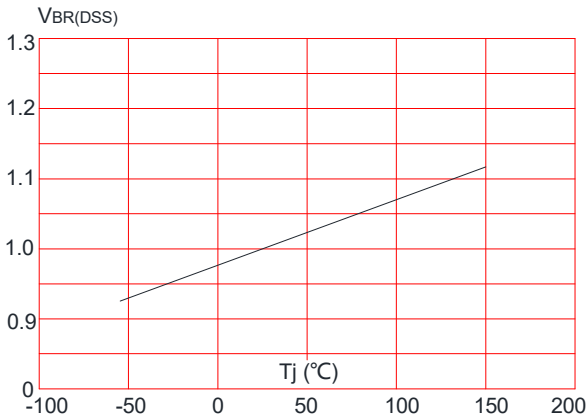


Figure 8: Normalized on Resistance vs. Junction Temperature

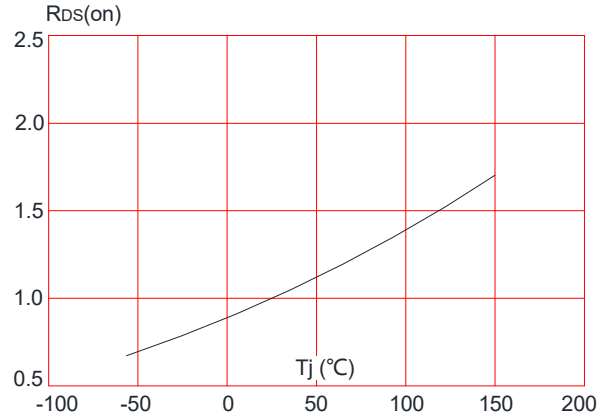


Figure 9: Maximum Safe Operating Area

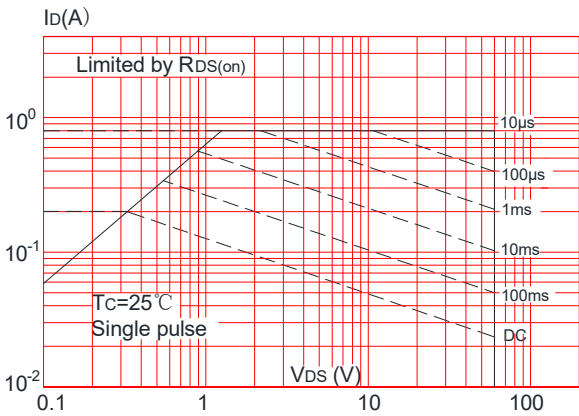


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

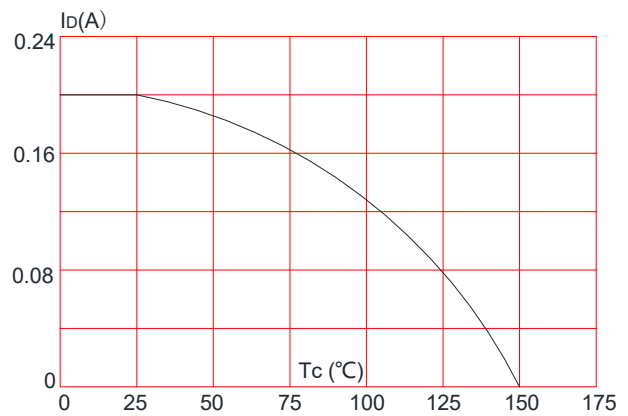
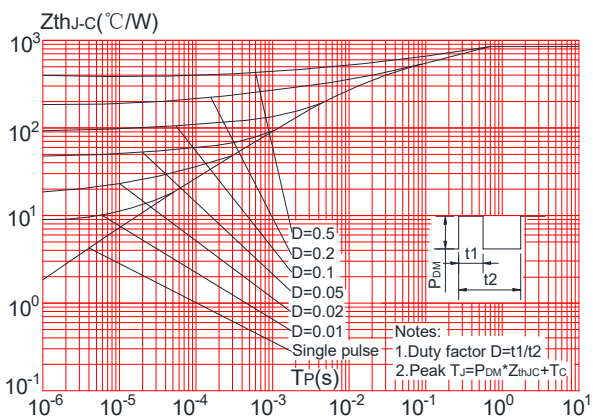


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



Test Circuit

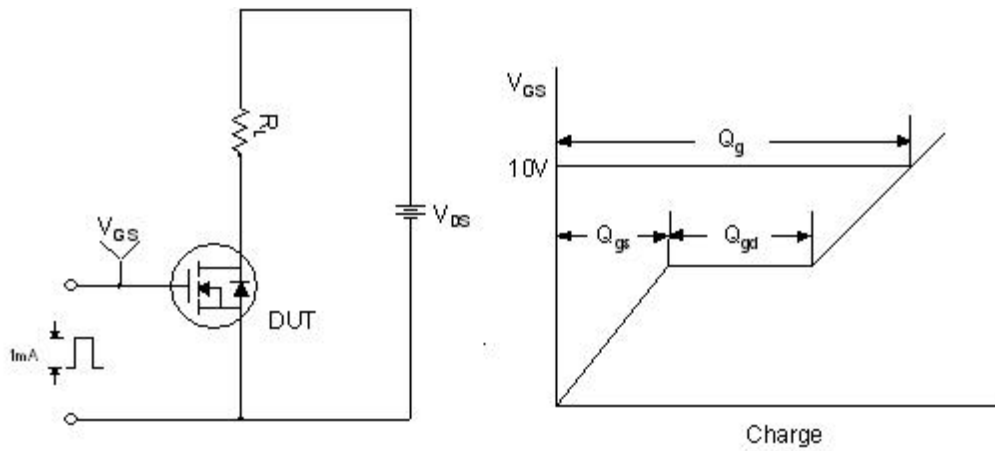


Figure 1. Gate Charge Test Circuit & Waveform

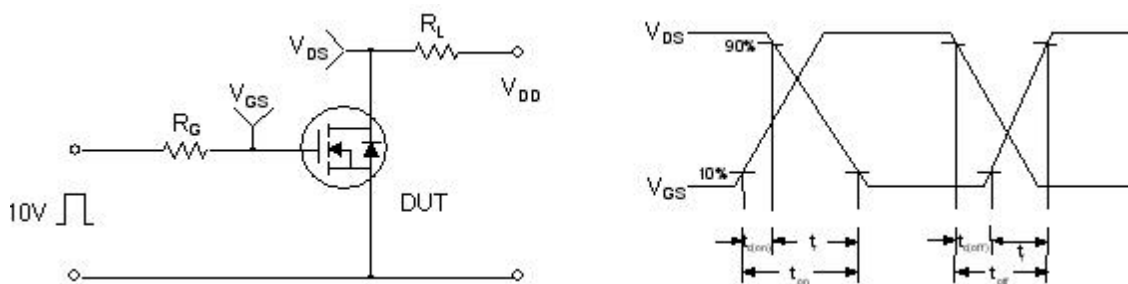


Figure 2. Resistive Switching Test Circuit & Waveforms

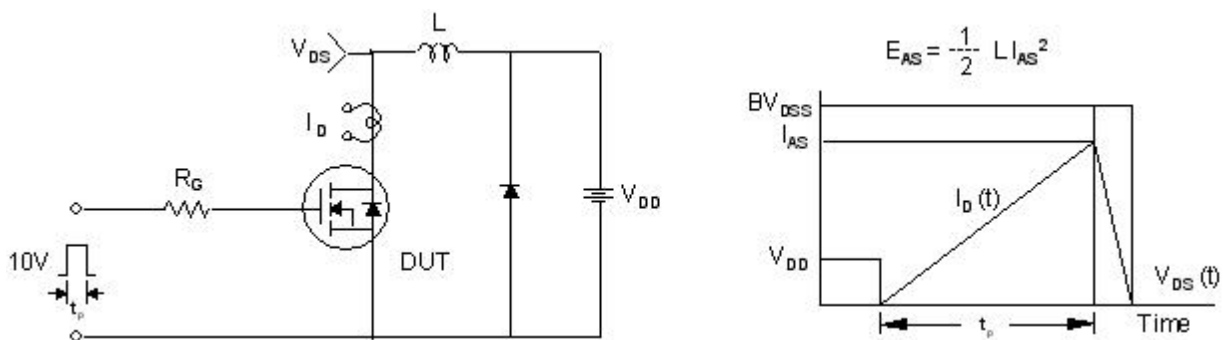
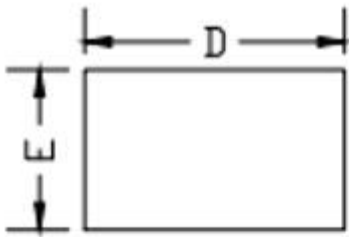
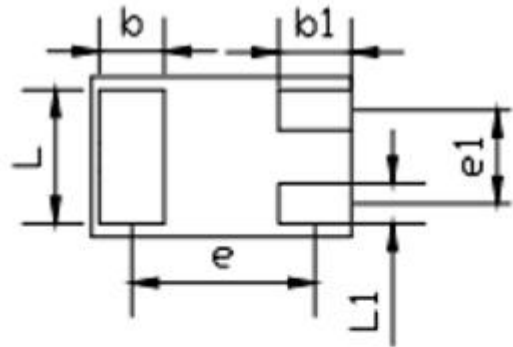


Figure 3. Unclamped Inductive Switching Test Circuit & Waveforms

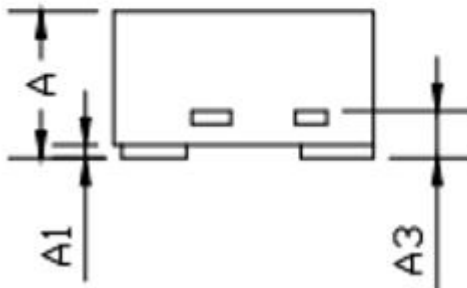
Package Mechanical Data-DFN1006-3L



TOP VIEW

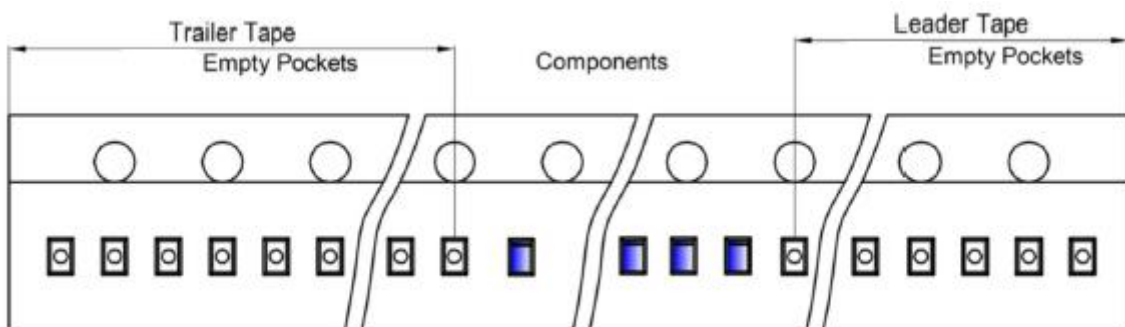


BOTTOM VIEW



SIDE VIEW

COMMON DIMENSION (MM)			
PKG	DFN1006		
REF.	MIN.	NOM.	MAX.
A	>0.4	-	0.50
A1	0.00	-	0.05
A3	0.127REF.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
b1	0.20	0.30	0.40
L	0.45	0.50	0.55
L1	0.10	0.15	0.20
e	0.675		
e1	0.35		






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